

# Vladimir Gavrilenko

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	3.3 THz Quantum Cascade Laser Based on a Three GaAs/AlGaAs Quantum-Well Active Module with an Operating Temperature above 120 K. <i>Semiconductors</i> , 2022, 56, 71-77.	0.2	1
2	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. <i>Technical Physics Letters</i> , 2021, 47, 154-157.	0.2	1
3	Feasibility of lasing in the GaAs Reststrahlen band with HgTe multiple quantum well laser diodes. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 175108.	1.3	4
4	Photothermal Ionization Spectroscopy of Mercury Vacancies in HgCdTe Epitaxial Films. <i>JETP Letters</i> , 2021, 113, 402-408.	0.4	3
5	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. <i>Journal of Applied Physics</i> , 2021, 129, .	1.1	11
6	Optical Studies and Transmission Electron Microscopy of HgCdTe Quantum Well Heterostructures for Very Long Wavelength Lasers. <i>Nanomaterials</i> , 2021, 11, 1855.	1.9	6
7	Terahertz plasmons in doped HgTe quantum well heterostructures: dispersion, losses, and amplification. <i>Applied Optics</i> , 2021, 60, 8991.	0.9	3
8	Stimulated emission of plasmon-LO mode in narrow gap HgTe/CdHgTe quantum wells. <i>Journal of Optics (United Kingdom)</i> , 2021, 23, 115001.	1.0	5
9	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. <i>Laser Physics</i> , 2021, 31, 015801.	0.6	7
10	Far-infrared stimulated emission of Dirac fermions in CdHgTe heterostructures. , 2021, , .		0
11	Coherent Emission in the Vicinity of 10 THz due to Auger-Suppressed Recombination of Dirac Fermions in HgCdTe Quantum Wells. <i>ACS Photonics</i> , 2021, 8, 3526-3535.	3.2	17
12	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at $\lambda \approx 4.6 \mu\text{m}$ wavelength from HgCdTe quantum wells. <i>Journal of Applied Physics</i> , 2021, 130, .		7
13	Generation of Terahertz Radiation in InP:Fe Crystals Due to Second-Order Lattice Nonlinearity. <i>Semiconductors</i> , 2021, 55, 785-789.	0.2	0
14	Effect of Internal Optical Losses on the Generation of Mid-IR Stimulated Emission in Waveguide Heterostructures with HgCdTe/CdHgTe Quantum Wells. <i>Semiconductors</i> , 2021, 55, 899-902.	0.2	0
15	Sub-terahertz FET detector with self-assembled Sn-nanowires. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 075102.	1.3	7
16	Fundamental Limits to Far-Infrared Lasing in Auger-Suppressed HgCdTe Quantum Wells. <i>ACS Photonics</i> , 2020, 7, 98-104.	3.2	21
17	Investigation of the Photosensitivity of Narrow-Gap and Gapless HgCdTe Solid Solutions in the Terahertz and Sub-Terahertz Range. <i>Semiconductors</i> , 2020, 54, 1096-1102.	0.2	1
18	Calculation of Wave Functions of Resonant Acceptor States in Narrow-Gap CdHgTe Compounds. <i>Semiconductors</i> , 2020, 54, 827-831.	0.2	4

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19	Probing States of a Double Acceptor in CdHgTe Heterostructures via Optical Gating. JETP Letters, 2020, 111, 575-581.	0.4	5
20	Temperature limitations for stimulated emission in $3\text{--}4\ \mu\text{m}$ range due to threshold and non-threshold Auger recombination in HgTe/CdHgTe quantum wells. Applied Physics Letters, 2020, 117, 083103.	1.5	20
21	Continuous-Wave Stimulated Emission in the $10\text{--}14\ \mu\text{m}$ Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. Semiconductors, 2020, 54, 1371-1375.	0.2	2
22	Photoluminescence Spectra of InAs/GaSb/InAs Quantum Wells in the Mid-Infrared Region. Semiconductors, 2020, 54, 1119-1122.	0.2	1
23	Terahertz Emission from HgCdTe QWs under Long-Wavelength Optical Pumping. Journal of Infrared, Millimeter, and Terahertz Waves, 2020, 41, 750-757.	1.2	3
24	Plasmon recombination in narrowgap HgTe quantum wells. Journal of Physics Communications, 2020, 4, 115012.	0.5	9
25	Specific Growth Features of Nanostructures for Terahertz Quantum Cascade Lasers and Their Physical Properties. Semiconductors, 2020, 54, 1092-1095.	0.2	5
26	Investigation of Stimulated Emission from HgTe/CdHgTe Quantum-Well Heterostructures in the $3\text{--}5\ \mu\text{m}$ Atmospheric Transparency Window. Semiconductors, 2020, 54, 1365-1370.	0.2	0
27	Mid-infrared stimulated emission in HgCdTe/CdHgTe quantum well heterostructures at room temperature. Optical Engineering, 2020, 60, .	0.5	5
28	Urbach tail and nonuniformity probe of HgCdTe thin films and quantum well heterostructures grown by molecular beam epitaxy. Optical Engineering, 2020, 60, .	0.5	4
29	Effects of the Electron-Electron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. JETP Letters, 2020, 112, 508-512.	0.4	1
30	Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. JETP Letters, 2019, 109, 657-662.	0.4	10
31	Magneto-transport in inverted HgTe quantum wells. Npj Quantum Materials, 2019, 4, .	1.8	16
32	Residual-Photoconductivity Spectra in HgTe/CdHgTe Quantum-Well Heterostructures. Semiconductors, 2019, 53, 1363-1366.	0.2	4
33	Balance-equation method for simulating terahertz quantum-cascade lasers using a wave-function basis with reduced dipole moments of tunnel-coupled states. Quantum Electronics, 2019, 49, 913-918.	0.3	15
34	Far and Mid IR Stimulated Emission in HgCdTe QW Heterostructures. , 2019, , .		1
35	Second-Harmonic Generation of Subterahertz Gyrotron Radiation by Frequency Doubling in InP:Fe and Its Application for Magneto-spectroscopy of Semiconductor Structures. Semiconductors, 2019, 53, 1217-1221.	0.2	6
36	Evolution of the Impurity Photoconductivity in CdHgTe Epitaxial Films with Temperature. Semiconductors, 2019, 53, 1266-1271.	0.2	2

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37	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd <sub>0.7</sub> Hg <sub>0.3</sub> Te QWs Near 14 $\mu$ m. Semiconductors, 2019, 53, 1154-1157.	0.2	4
38	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. JETP Letters, 2019, 109, 96-101.	0.4	4
39	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. JETP Letters, 2019, 109, 191-197.	0.4	2
40	Carrier Recombination, Long-Wavelength Photoluminescence, and Stimulated Emission in HgCdTe Quantum Well Heterostructures. Physica Status Solidi (B): Basic Research, 2019, 256, 1800546.	0.7	15
41	Massless Dirac fermions in III-V semiconductor quantum wells. Physical Review B, 2019, 99, .	1.1	14
42	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. Condensed Matter, 2019, 4, 27.	0.8	5
43	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. Journal of Physics Condensed Matter, 2019, 31, 145501.	0.7	13
44	Chain of Dirac spectrum loops of nodes in crossed magnetic and electric fields. Physical Review B, 2018, 97, .	1.1	6
45	Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. Journal of Experimental and Theoretical Physics, 2018, 127, 1125-1129.	0.2	6
46	Terahertz Injection Lasers Based on a PbSnSe Solid Solution with an Emission Wavelength up to 50 $\mu$ m and Their Application in the Magneto Spectroscopy of Semiconductors. Semiconductors, 2018, 52, 1590-1594.	0.2	14
47	Bipolar Persistent Photoconductivity in HgTe/CdHgTe (013) Double Quantum-Well Heterostructures. Semiconductors, 2018, 52, 1586-1589.	0.2	9
48	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. JETP Letters, 2018, 108, 329-334.	0.4	4
49	HgCdTe based quantum well heterostructures for long-wavelength lasers operating in 5 - 15 THz range. Journal of Physics: Conference Series, 2018, 1092, 012126.	0.3	0
50	Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. Sensors, 2018, 18, 4341.	2.1	4
51	HgTe/CdTe Quantum Well Heterostructures For Far and Mid IR Lasers. , 2018, , .		0
52	Magneto-optics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. Semiconductors, 2018, 52, 1386-1391.	0.2	4
53	Temperature Dependences of the Threshold Current and Output Power of a Quantum-Cascade Laser Emitting at 3.3 THz. Semiconductors, 2018, 52, 1380-1385.	0.2	14
54	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. Journal of Physics Condensed Matter, 2018, 30, 495301.	0.7	22

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55	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. Semiconductors, 2018, 52, 1375-1379.	0.2	6
56	Calculation of Multiply Charged States of Impurity-Defect Centers in Epitaxial Hg <sub>1-x</sub> CdxTe Layers. Semiconductors, 2018, 52, 1369-1374.	0.2	4
57	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. Physical Review B, 2018, 97, .	1.1	24
58	Stimulated emission in the 28-35 $\mu$ m wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. Optics Express, 2018, 26, 12755.	1.7	26
59	Magneto-optical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. Semiconductors, 2018, 52, 436-441.	0.2	0
60	Cyclotron resonance of Dirac fermions in InAs/GaSb/InAs quantum wells. Semiconductors, 2017, 51, 38-42.	0.2	3
61	Terahertz radiation generation in multilayer quantum-cascade heterostructures. Technical Physics Letters, 2017, 43, 362-365.	0.2	24
62	HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, .	2.2	49
63	Activation conductivity in HgTe/CdHgTe quantum wells at integer Landau level filling factors: Role of the random potential. Semiconductors, 2017, 51, 1562-1570.	0.2	0
64	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. Semiconductors, 2017, 51, 1531-1536.	0.2	8
65	Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to 19.5 $\mu$ m. Applied Physics Letters, 2017, 111, .	1.5	58
66	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. Physical Review B, 2017, 96, .	1.1	38
67	Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. Semiconductor Science and Technology, 2017, 32, 095007.	1.0	27
68	Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. Semiconductors, 2017, 51, 1557-1561.	0.2	6
69	Detector for terahertz applications based on a serpentine array of integrated GaAs/InGaAs/AlGaAs-field-effect transistors. , 2017, , .		0
70	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs $\epsilon$ -Three-Layer $\epsilon$ -Gapless Quantum Wells. JETP Letters, 2017, 106, 727-732.	0.4	5
71	Temperature-driven massless fermions in HgCdTe heterostructures. , 2017, , .		0
72	Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 534-537.	0.8	2

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73	Pressure- and temperature-driven phase transitions in HgTe quantum wells. Physical Review B, 2016, 94, .	1.1	57
74	Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. Semiconductors, 2016, 50, 1651-1656.	0.2	7
75	Long wavelength stimulated emission up to 9.5 $\mu\text{m}$ from HgCdTe quantum well heterostructures. Applied Physics Letters, 2016, 108, .	1.5	34
76	Temperature-driven massless Kane fermions in HgCdTe crystals. , 2016, , .		2
77	Terahertz cyclotron emission from HgCdTe bulk films. , 2016, , .		0
78	Terahertz Response of Tightly Concatenated Two Dimensional InGaAs Field-Effect Transistors Integrated on a Single Chip. International Journal of High Speed Electronics and Systems, 2016, 25, 1640012.	0.3	0
79	Mercury vacancies as divalent acceptors in $\text{Hg}_{1-y}\text{Te}/\text{Cd}_{1-x}\text{Hg}_x\text{Te}$ structures with quantum wells. Semiconductors, 2016, 50, 1662-1668.	0.2	6
80	THz magnetospectroscopy of double HgTe quantum well. , 2016, , .		0
81	Terahertz imaging of Landau levels in HgTe-based topological insulators. Applied Physics Letters, 2016, 108, .	1.5	13
82	Long-wavelength stimulated emission in HgCdTe quantum well waveguide heterostructures. , 2016, , .		0
83	The study of the laser characteristics based on solid solution $\text{Pb}_{1-x}\text{Sn}_x\text{Se}$ ( $x \approx 0.07$ ) emitting at spectral range of 16 $\mu\text{m}$ . Journal of Physics: Conference Series, 2016, 740, 012005.	0.3	0
84	Detection of terahertz radiation by array of integrated field-effect transistors with floating electrodes. , 2016, , .		0
85	Terahertz emission from CdHgTe/HgTe quantum wells with an inverted band structure. Semiconductors, 2016, 50, 915-919.	0.2	2
86	Variation of the emission frequency of a terahertz quantum cascade laser. Technical Physics Letters, 2016, 42, 230-233.	0.2	0
87	Magnetospectroscopy of double HgTe/CdHgTe quantum wells. Semiconductors, 2016, 50, 1532-1538.	0.2	9
88	Temperature-driven massless Kane fermions in HgCdTe crystals. Nature Communications, 2016, 7, 12576.	5.8	73
89	Temperature-dependent magnetospectroscopy of HgTe quantum wells. Physical Review B, 2016, 94, .	1.1	21
90	Terahertz injection lasers based on PbSnSe alloy with an emission wavelength up to 46.5 $\mu\text{m}$ . Semiconductors, 2016, 50, 1669-1672.	0.2	7

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91	Effective Third-Order Nonlinearities in Refractory Plasmonic TiN Thin Films. , 2016, , .		1
92	Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. Semiconductors, 2015, 49, 1627-1633.	0.2	6
93	Long-wavelength injection lasers based on Pb <sub>1-x</sub> Sn <sub>x</sub> Se alloys and their use in solid-state spectroscopy. Semiconductors, 2015, 49, 1623-1626.	0.2	16
94	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. Selected Topics in Electronics and Systems, 2015, , 31-53.	0.2	1
95	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. Applied Physics Letters, 2015, 107, .	1.5	13
96	Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. Journal of Physics: Conference Series, 2015, 647, 012008.	0.3	6
97	Investigation of magnetoabsorption at different temperatures in HgTe/CdHgTe quantum-well heterostructures in pulsed magnetic fields. Semiconductors, 2015, 49, 1611-1615.	0.2	5
98	Impurity-induced photoconductivity of narrow-gap Cadmiumâ€“Mercuryâ€“Telluride structures. Semiconductors, 2015, 49, 1605-1610.	0.2	6
99	Cyclotron resonance in InAs/AlSb quantum wells in magnetic fields up to 45 T. Semiconductors, 2015, 49, 1616-1622.	0.2	0
100	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. International Journal of High Speed Electronics and Systems, 2015, 24, 1550002.	0.3	6
101	An array of integrated on a chip GaAs/InGaAs/AlGaAs-field-effect transistors with floating electrodes for detection of terahertz radiation. , 2015, , .		0
102	Exchange enhancement of the electron g factor in strained InGaAs/InP heterostructures. Semiconductors, 2015, 49, 191-198.	0.2	5
103	Effect of the direct capture of holes with the emission of optical phonons on impurity-photoconductivity relaxation in p-Si:B. Semiconductors, 2015, 49, 187-190.	0.2	4
104	Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. JETP Letters, 2015, 100, 790-794.	0.4	26
105	Long wavelength superluminescence from narrow gap HgCdTe epilayer at 100â€“K. Applied Physics Letters, 2015, 107, .	1.5	11
106	Infrared magneto-spectroscopy of two-dimensional and three-dimensional massless fermions: A comparison. Journal of Applied Physics, 2015, 117, 112803.	1.1	7
107	Effect of electron-electron interaction on cyclotron resonance in high-mobility InAs/AlSb quantum wells. Journal of Applied Physics, 2015, 117, 112813.	1.1	16
108	Effective third-order nonlinearities in metallic refractory titanium nitride thin films. Optical Materials Express, 2015, 5, 2395.	1.6	50

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109	Detection of terahertz radiation by tightly concatenated InGaAs field-effect transistors integrated on a single chip. Applied Physics Letters, 2014, 104, 163508.	1.5	10
110	Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. Nature Physics, 2014, 10, 233-238.	6.5	190
111	Efficient long wavelength interband photoluminescence from HgCdTe epitaxial films at wavelengths up to 26 $\mu\text{m}$ . Applied Physics Letters, 2014, 104, .	1.5	35
112	Time resolved photoluminescence spectroscopy of narrow gap Hg <sub>1-x</sub> Cd <sub>x</sub> Te/Cd <sub>y</sub> Hg <sub>1-y</sub> Te quantum well heterostructures. Applied Physics Letters, 2014, 105, 022102.	1.5	28
113	Terahertz detector with series connection of asymmetric gated transistors. Journal of Physics: Conference Series, 2014, 486, 012016.	0.3	0
114	Specific features of the spectra and relaxation kinetics of long-wavelength photoconductivity in narrow-gap HgCdTe epitaxial films and heterostructures with quantum wells. Semiconductors, 2013, 47, 1438-1441.	0.2	18
115	Magnetoabsorption in narrow-gap HgCdTe epitaxial layers in the terahertz range. Semiconductors, 2013, 47, 1545-1550.	0.2	6
116	Relaxation kinetics of impurity photoconductivity in p-Si:B with various levels of doping and degrees of compensation in high electric fields. Semiconductors, 2013, 47, 1461-1464.	0.2	3
117	Rashba spin splitting and cyclotron resonance in strained InGaAs/InP heterostructures with a two-dimensional electron gas. Semiconductors, 2013, 47, 1485-1491.	0.2	7
118	Type II $\rightarrow$ type I conversion of GaAs/GaAsSb heterostructure energy spectrum under optical pumping. Journal of Applied Physics, 2013, 113, 163107.	1.1	15
119	Exchange interaction and rashba spin splitting effects in electron spin resonance in narrow-gap quantum wells. , 2013, , .		0
120	Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. Journal of Physics: Conference Series, 2013, 461, 012038.	0.3	1
121	Spin-wave excitations and electron spin resonance in symmetric and asymmetric narrow-gap quantum wells. Physical Review B, 2013, 87, .	1.1	14
122	Terahertz magnetospectroscopy of narrow-gap HgCdTe-based structures. , 2013, , .		0
123	Spectra and kinetics of THz photoconductivity in narrow-gap Hg <sub>1-x</sub> Cd <sub>x</sub> Te (x < 0.2) epitaxial films. Semiconductor Science and Technology, 2013, 28, 125007.	1.0	29
124	Effects of Rashba spin splitting and exchange interaction in electron spin resonance in narrow-gap quantum well heterostructures. Journal of Physics: Conference Series, 2013, 456, 012021.	0.3	1
125	Exchange enhancement of quasiparticle and ESR spin-gap in symmetric and asymmetric narrow-gap quantum wells. Journal of Physics: Conference Series, 2013, 461, 012037.	0.3	0
126	The effect of exchange interaction on quasiparticle Landau levels in narrow-gap quantum well heterostructures. Journal of Physics Condensed Matter, 2012, 24, 135601.	0.7	9



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127	Cyclotron resonance in HgTe/CdTe-based heterostructures in high magnetic fields. <i>Nanoscale Research Letters</i> , 2012, 7, 534.	3.1	47
128	Cyclotron resonance study in InAs/AlSb quantum well heterostructures with two occupied electronic subbands. <i>Journal of Applied Physics</i> , 2012, 111, 093711.	1.1	16
129	Study of lifetimes and photoconductivity relaxation in heterostructures with Hg <sub>x</sub> Cd <sub>1-x</sub> Te/Cd <sub>y</sub> Hg <sub>1-y</sub> Te quantum wells. <i>Semiconductors</i> , 2012, 46, 1362-1366.	0.2	34
130	Determination of the heterojunction type in structures with GaAsSb/GaAs quantum wells with various antimony fractions by optical methods. <i>Semiconductors</i> , 2012, 46, 1376-1380.	0.2	4
131	Features of impurity-photoconductivity relaxation in boron-doped silicon. <i>Semiconductors</i> , 2012, 46, 1387-1391.	0.2	14
132	Features of the persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells and a tunneling-transparent barrier. <i>Semiconductors</i> , 2012, 46, 1396-1401.	0.2	18
133	Diagnostics of quantum cascade structures by optical methods in the near infrared region. <i>Semiconductors</i> , 2012, 46, 1411-1414.	0.2	2
134	Rashba spin splitting and exchange enhancement of the g factor in InAs/AlSb heterostructures with a two-dimensional electron gas. <i>Semiconductors</i> , 2012, 46, 1163-1170.	0.2	18
135	Exchange interaction effects in electron spin resonance: Larmor theorem violation in narrow-gap quantum well heterostructures. <i>Journal of Physics Condensed Matter</i> , 2012, 24, 252201.	0.7	8
136	Experimental study of frequency multipliers based on a GaAs/AlAs semiconductor superlattices in the terahertz frequency range. <i>Semiconductors</i> , 2012, 46, 121-125.	0.2	43
137	Studying the frequency tuning of pulsed terahertz quantum cascade lasers. <i>Radiophysics and Quantum Electronics</i> , 2012, 54, 609-615.	0.1	5
138	Cyclotron resonance in HgTe/CdTe(013) narrowband heterostructures in quantized magnetic fields. <i>JETP Letters</i> , 2012, 95, 406-410.	0.4	12
139	Theory of g-factor enhancement in narrow-gap quantum well heterostructures. <i>Journal of Physics Condensed Matter</i> , 2011, 23, 385601.	0.7	19
140	High-responsivity terahertz detection by on-chip InGaAs/GaAs field-effect-transistor array. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	49
141	Cyclotron resonance and interband optical transitions in HgTe/CdTe(001) quantum well heterostructures. <i>Semiconductor Science and Technology</i> , 2011, 26, 125011.	1.0	43
142	Electron-electron interaction and spin-orbit coupling in InAs/AlSb heterostructures with a two-dimensional electron gas. <i>Semiconductors</i> , 2011, 45, 110-117.	0.2	20
143	Relaxation of the impurity photoconductivity in p-Ge/Ge <sub>1-x</sub> Si <sub>x</sub> quantum well heterostructures. <i>Semiconductor Science and Technology</i> , 2011, 26, 085009.	1.0	4
144	GaAsSb/GaAs strained structures with quantum wells for lasers with emission wavelength near 1.3 μm. <i>Semiconductors</i> , 2010, 44, 405-412.	0.2	27

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145	Persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells. Semiconductors, 2010, 44, 616-622.	0.2	24
146	Terahertz emission and photoconductivity in n-type GaAs/AlGaAs quantum wells: the role of resonant impurity states. Semiconductors, 2010, 44, 1394-1397.	0.2	14
147	High-resolution emission spectra of pulsed terahertz quantum-cascade lasers. Semiconductors, 2010, 44, 1467-1471.	0.2	3
148	Kinetics of terahertz photoconductivity in p-Ge under impurity breakdown conditions. Semiconductors, 2010, 44, 1476-1479.	0.2	10
149	The cyclotron resonance of holes in InGaAs/GaAs heterostructures with quantum wells in quantizing magnetic fields. Semiconductors, 2010, 44, 1492-1494.	0.2	7
150	Wide-aperture detector of terahertz radiation based on GaAs/InGaAs transistor structure with large-area slit grating gate. Technical Physics Letters, 2010, 36, 365-368.	0.2	11
151	Cyclotron Resonance of Extremely Conductive 2D Holes in High Ge Content Strained Heterostructures. Journal of Low Temperature Physics, 2010, 159, 216-221.	0.6	4
152	Spin splitting in HgTe/CdHgTe (013) quantum well heterostructures. JETP Letters, 2010, 92, 63-66.	0.4	23
153	Terahertz spectroscopy of quantum-well narrow-bandgap HgTe/CdTe-based heterostructures. JETP Letters, 2010, 92, 756-761.	0.4	27
154	Resonance detection of terahertz radiation in nanometer field-effect transistors with two-dimensional electron gas. , 2010, , .		0
155	Terahertz emission from GaN epilayers at lateral electric field. , 2010, , .		0
156	High-field splitting of the cyclotron resonance absorption in strained $\text{InGaAs/GaAs}$ quantum wells. Physical Review B, 2009, 79, .	1.1	19
157	Impurity breakdown and terahertz luminescence in n-GaN epilayers under external electric field. Journal of Applied Physics, 2009, 106, 123523.	1.1	26
158	Emission spectra of terahertz quantum cascade laser. Radiophysics and Quantum Electronics, 2009, 52, 494-499.	0.1	2
159	Fano resonances in the impurity photocurrent spectra of GaAs samples and an InGaAs/GaAsP quantum-well heterostructure doped with shallow acceptors. Journal of Experimental and Theoretical Physics, 2009, 109, 466-471.	0.2	3
160	Difference-frequency generation in a butt-join diode laser. Semiconductors, 2009, 43, 208-211.	0.2	4
161	Evolution of the photoresponse time of the GaAs/AlGaAs cyclotron resonance quantum Hall effect detector. Semiconductors, 2009, 43, 223-227.	0.2	0
162	Resonance detection of terahertz radiation in submicrometer field-effect GaAs/AlGaAs transistors with two-dimensional electron gas. Semiconductors, 2009, 43, 528-531.	0.2	3

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